18.D8 We are asked to compare silicon and gallium arsenide semiconductors relative to properties and applications.

The following are the characteristics and applications for Si: (1) being an elemental semiconductor, it is cheaper to grow in single-crystalline form; (2) because of its electron band structure, it is best used in transistors; (3) electronic processes are relatively slow due to the low mobilities for electrons and holes (Table 18.3).

For GaAs: (1) it is much more expensive to produce inasmuch as it is a compound semiconductor; (2) because of its electron band structure it is best used in light-emitting diodes and semiconducting lasers; (3) its band gap may be altered by alloying; (4) electronic processes are more rapid than in Si due to the greater mobilities for electrons and holes; (5) absorption of electromagnetic radiation is greater in GaAs, and therefore, thinner layers are required for solar cells.

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